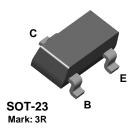


2N5771

MMBT5771





PNP Switching Transistor

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	15	V
V _{EBO}	Emitter-Base Voltage	4.5	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	М	Units	
		2N5771	*MMBT5771	
P_D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP Switching Transistor (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	15		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, V_{BE} = 0$	15		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \mu A, I_{E} = 0$	15		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	4.5		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 8.0 \text{ V}, I_{E} = 0$		10	nA
I _{CES}	Collector Cutoff Current	$V_{CE} = 8.0 \text{ V}, V_{BE} = 0$ $V_{CE} = 8.0 \text{ V}, V_{BE} = 0, T_{A} = 125^{\circ}\text{C}$		10 5.0	nA μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4.5 V, I _C = 0		1.0	μА
h _{FE}	DC Current Gain	$\begin{array}{l} I_{C} = 1.0 \text{ mA}, V_{CE} = 0.5 \text{ V} \\ I_{C} = 10 \text{ mA}, V_{CE} = 0.3 \text{ V} \\ I_{C} = 10 \text{mA}, V_{CE} = 0.3 \text{V}, T_{A} = -55^{\circ}\text{C} \\ I_{C} = 50 \text{ mA}, V_{CE} = 1.0 \text{ V} \end{array}$	35 50 20 40	120	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, V_C = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	-10	0.15 0.18 0.6	V V
$V_{\text{BE(sat)}}$	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.75	0.8 0.95 1.5	V V V
SMALL SI	GNAL CHARACTERISTICS				
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_{E} = 0,$ f = 140 kHz		3.0	pF
C _{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0,$ f = 140 kHz		3.5	pF
h _{fe}	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	8.5		
SWITCHI	NG CHARACTERISTICS				
ts	Storage Time	$I_C = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$ $I_{B1} = I_{B2} = 1.0 \text{ mA}$		20	ns
-3				1	1
t _{on}	Turn-On Time	$\begin{split} I_{C} &= 10 \text{ mA, } V_{CC} = 1.5 \text{ V,} \\ I_{B} &= 1.0 \text{ mA} \\ I_{C} &= 10 \text{ mA, } V_{CC} = 1.5 \text{ V,} \end{split}$		15	ns

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

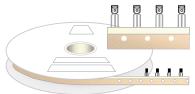
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

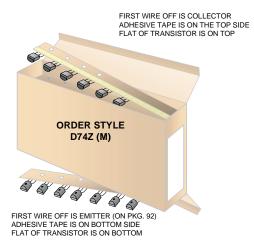


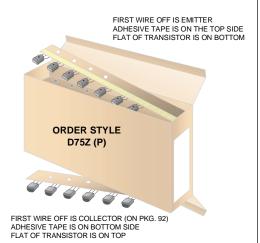
Style "A", D26Z, D70Z (s/h)

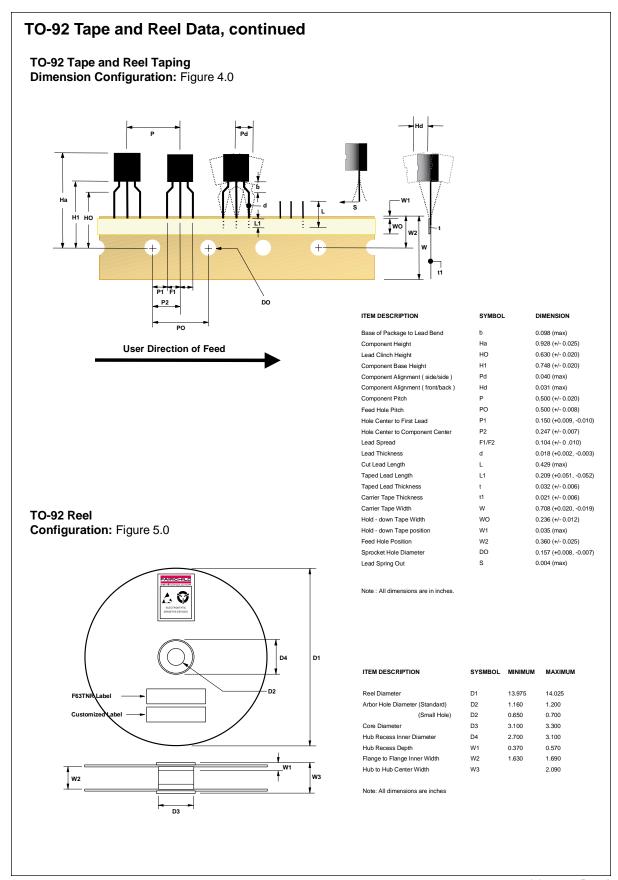
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



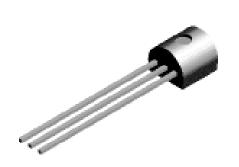


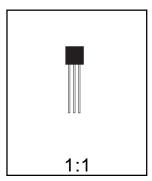


TO-92 Package Dimensions



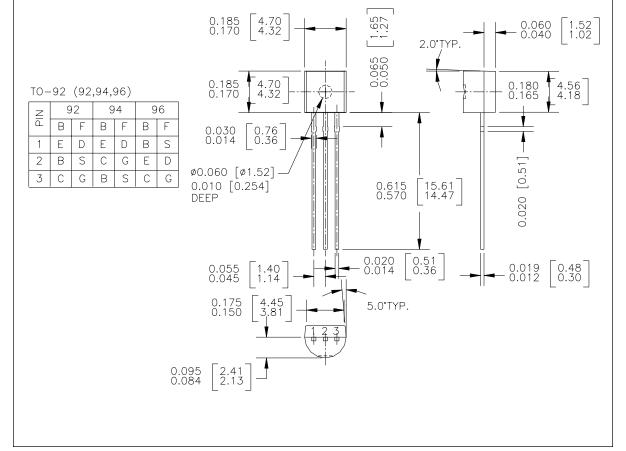
TO-92 (FS PKG Code 92, 94, 96)

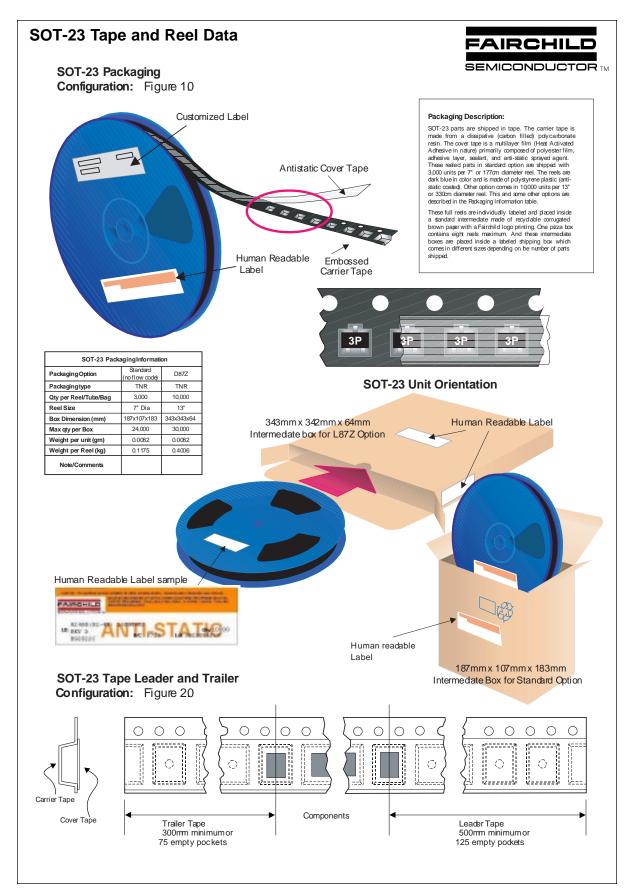




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

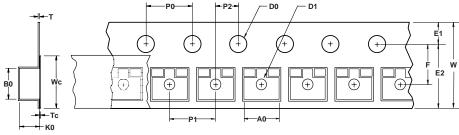




SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



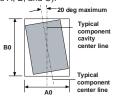
User Direction of Feed

					Di	mension	s are in n	nillimete	r					
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

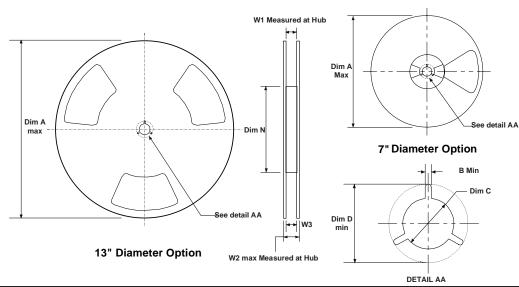


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

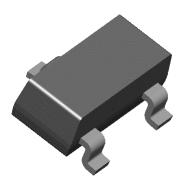
SOT-23 Reel Configuration: Figure 4.0

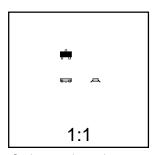


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



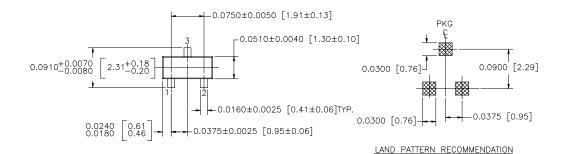
SOT-23 (FS PKG Code 49)

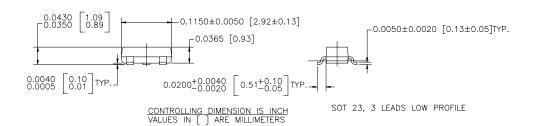




Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]
Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.					